

Product Summary

Device	BV _{DSS}	R _{DS(ON)} max	I _D Max T _A = +25°C
Q2	30V	21mΩ @ V _{GS} = 10V	8.5A
		32mΩ @ V _{GS} = 4.5V	7.2A
Q1	-30V	39mΩ @ V _{GS} = -10V	-7A
		53mΩ @ V _{GS} = -4.5V	-5.6A

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

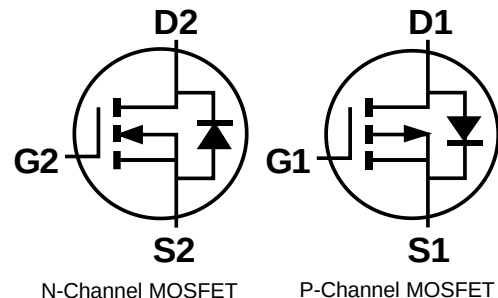
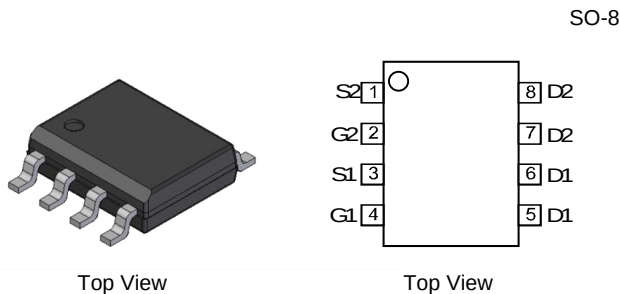
- Power Management Functions
- Analog Switch
- Load Switch

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.**
<https://www.diodes.com/quality/product-definitions/>
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMC3021LSDQ)**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.072 grams (Approximate)

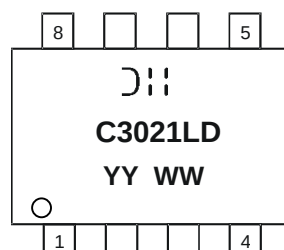


Ordering Information (Note 4)

Part Number	Case	Packaging
DMC3021LSD-13	SO-8	2500/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



DII = Manufacturer's Marking
C3021LD = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Year (ex: 20 = 2020)
WW = Week (01 to 53)

Maximum Ratings N-CHANNEL – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5)	Steady State	T _A = +25°C	I _D	8.5	A
		T _A = +85°C		7.1	
Pulsed Drain Current (Note 6)			I _{DM}	40	A

Maximum Ratings P-CHANNEL – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5)	Steady State	T _A = +25°C T _A = +85°C	I _D	-7.0 -4.5	A
Pulsed Drain Current (Note 6)			I _{DM}	-30	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	50	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics N-CHANNEL – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1.0	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	1.45	2.1	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	14	21	mΩ	V _{GS} = 10V, I _D = 7A
		—	18	32		V _{GS} = 4.5V, I _D = 5.6A
Forward Transfer Admittance	Y _{fs}	—	8.1	—	S	V _{DS} = 5V, I _D = 7A
Diode Forward Voltage (Note 7)	V _{SD}	—	0.7	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	767	—	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	110	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	105	—	pF	
Gate Resistance	R _g	—	1.4	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	7.8	—	nC	V _{DS} = 15V, I _D = 9A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	16.1	—	nC	
Gate-Source Charge	Q _{gs}	—	1.8	—	nC	
Gate-Drain Charge	Q _{gd}	—	2.5	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	5.0	—	ns	V _{GS} = 10V, V _{DS} = 15V, R _G = 6Ω, I _D = 1A
Turn-On Rise Time	t _r	—	4.5	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	26.3	—	ns	
Turn-Off Fall Time	t _f	—	8.55	—	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Repetitive rating, pulse width limited by junction temperature.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

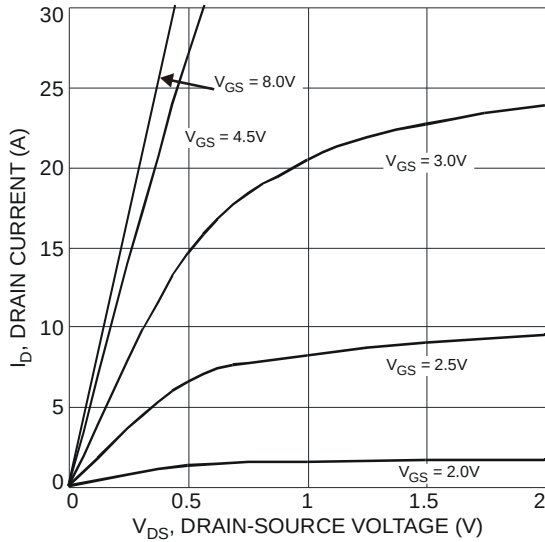


Fig. 1 Typical Output Characteristics

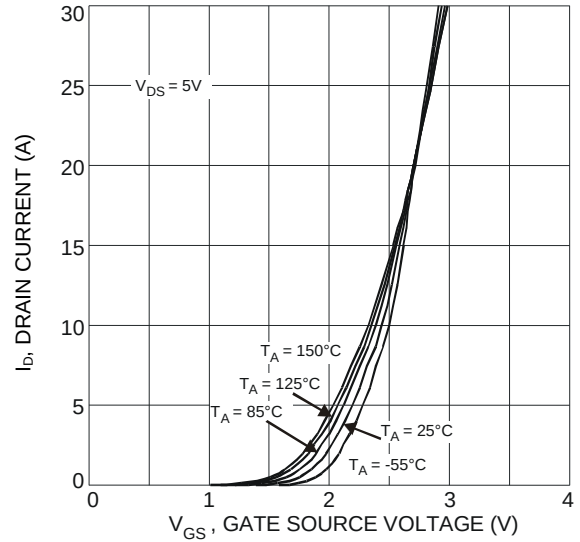


Fig. 2 Typical Transfer Characteristics

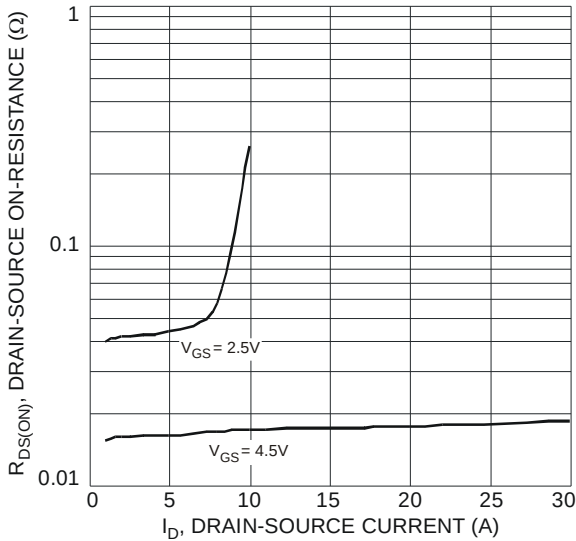


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

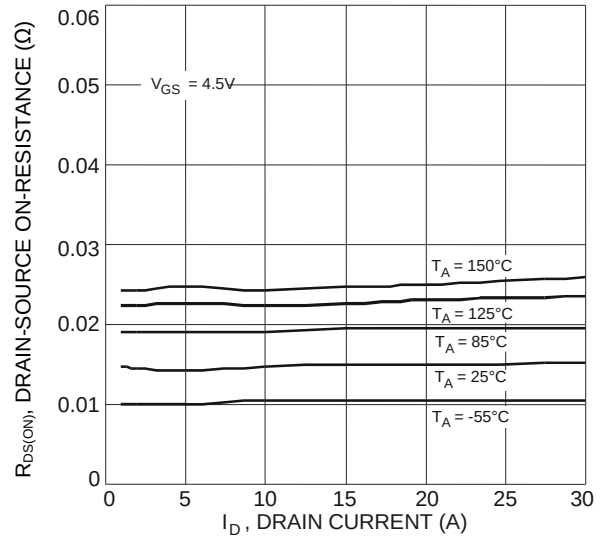


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

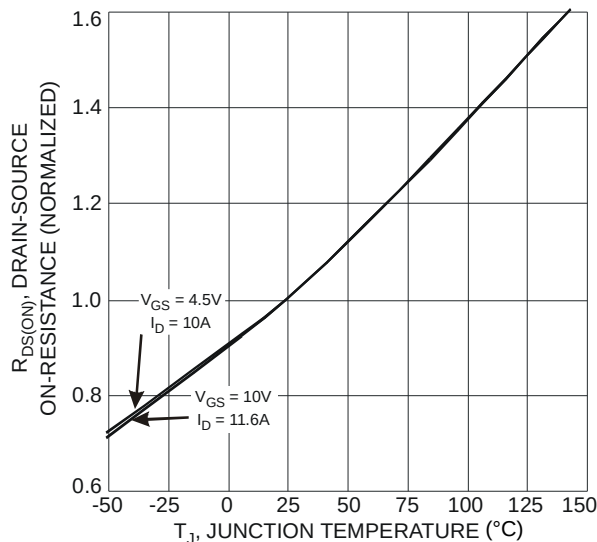


Fig. 5 On-Resistance Variation with Temperature

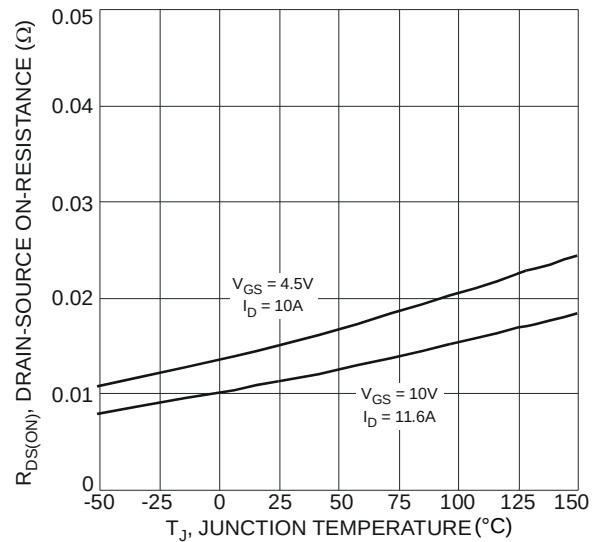


Fig. 6 On-Resistance Variation with Temperature

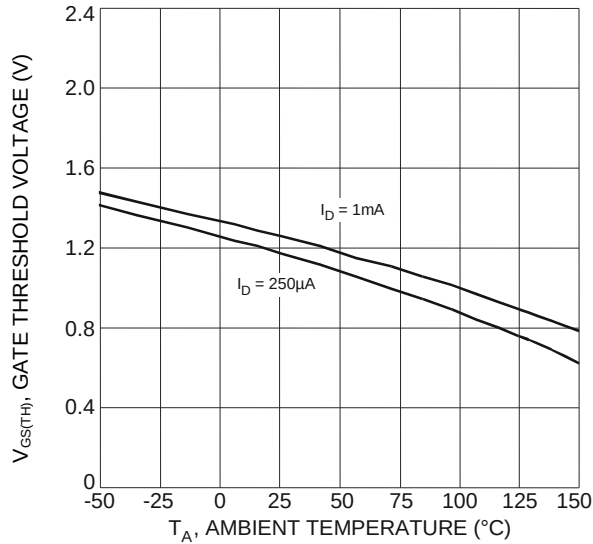


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

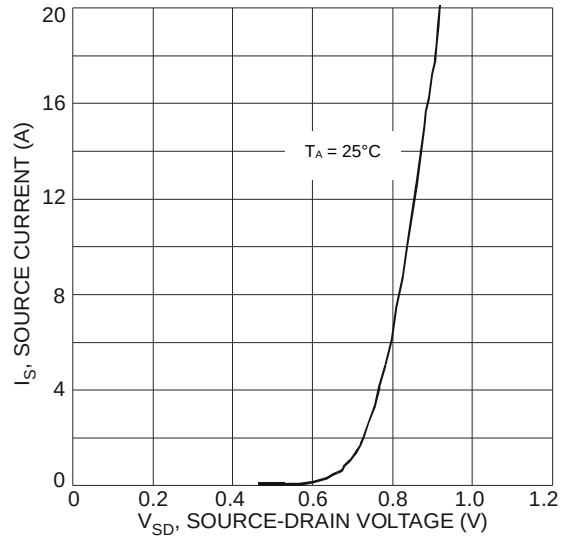


Fig. 8 Diode Forward Voltage vs. Current

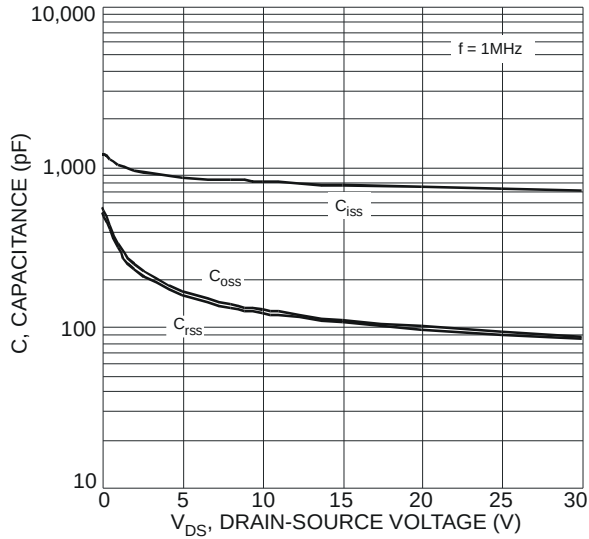


Fig. 9 Typical Capacitance

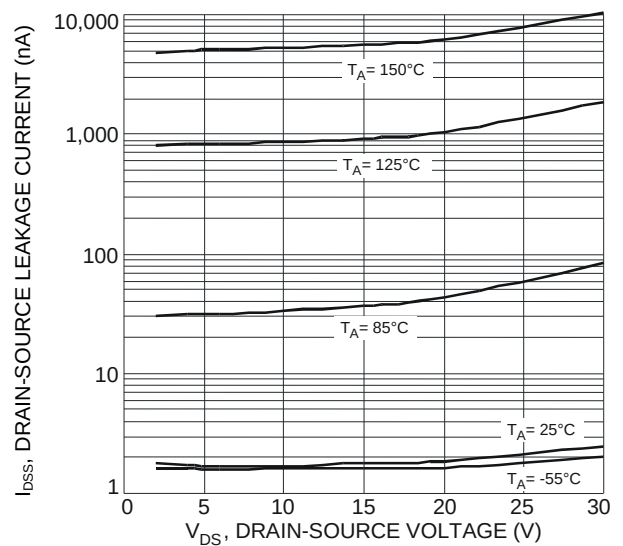


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

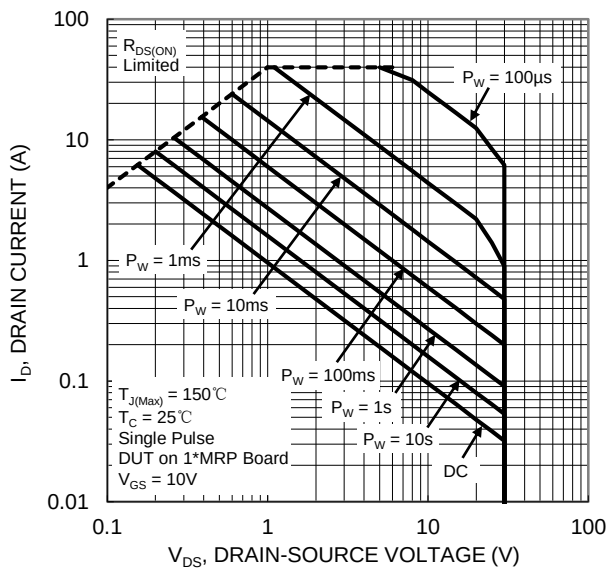


Fig. 11 SOA, Safe Operation Area

Electrical Characteristics P-CHANNEL – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1.0	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-1	-1.7	-2.2	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	30	39	mΩ	V _{GS} = -10V, I _D = -4.3A
			42	53		V _{GS} = -4.5V, I _D = -3.7A
Forward Transfer Admittance	Y _{fs}	—	7	—	S	V _{DS} = -5V, I _D = -4.3A
Diode Forward Voltage (Note 7)	V _{SD}	—	-0.75	-1.0	V	V _{GS} = 0V, I _S = -1.7A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	1002	—	pF	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	125	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	118	—	pF	
Gate Resistance	R _g	—	13	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	10.1	—	nC	V _{DS} = -15V, I _D = -6A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	21.1	—	nC	
Gate-Source Charge	Q _{gs}	—	2.8	—	nC	
Gate-Drain Charge	Q _{gd}	—	3.2	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	10.1	—	ns	V _{GS} = -10V, V _{DS} = -15V, R _G = 6Ω, I _D = -1A
Turn-On Rise Time	t _r	—	6.5	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	50.1	—	ns	
Turn-Off Fall Time	t _f	—	22.2	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.

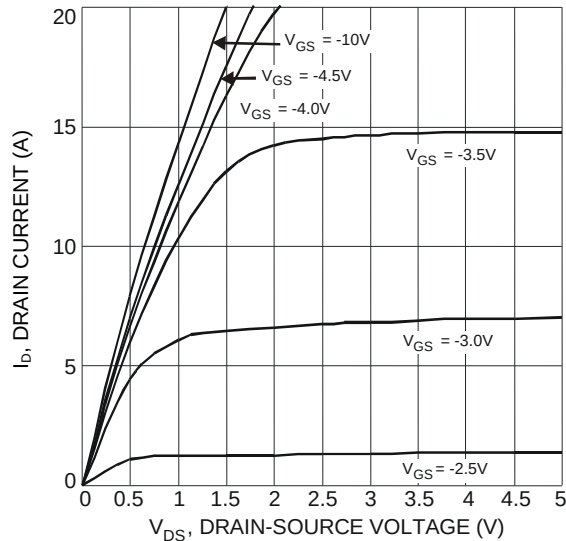


Fig. 12 Typical Output Characteristics

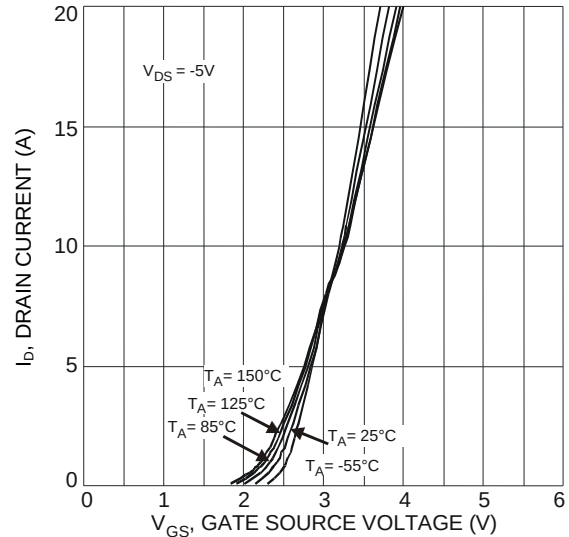


Fig. 13 Typical Transfer Characteristics

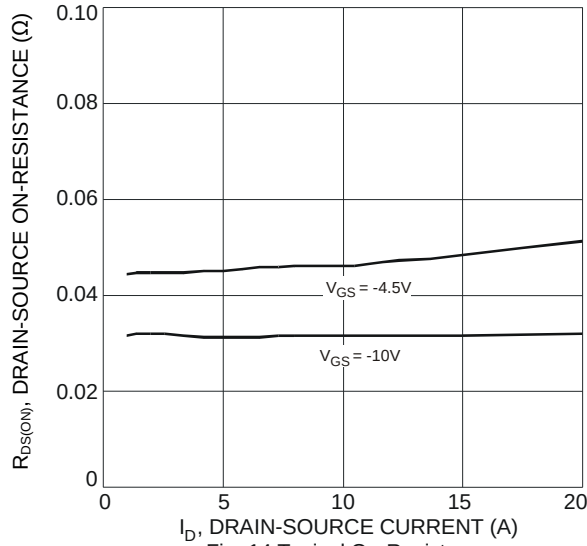


Fig. 14 Typical On-Resistance vs. Drain Current and Gate Voltage

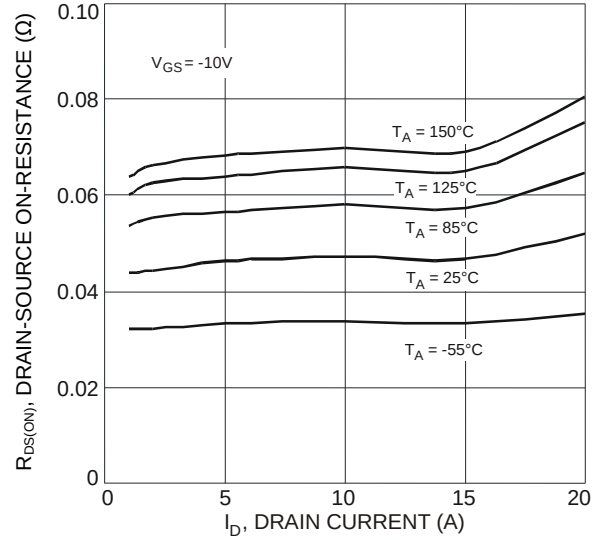


Fig. 15 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

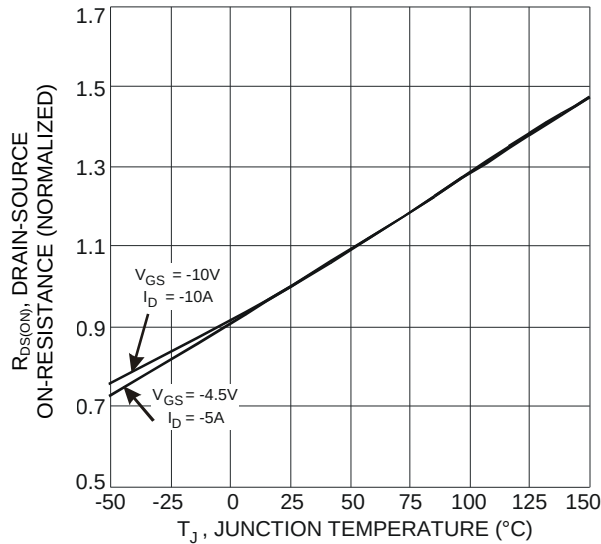


Fig. 16 On-Resistance Variation with Temperature

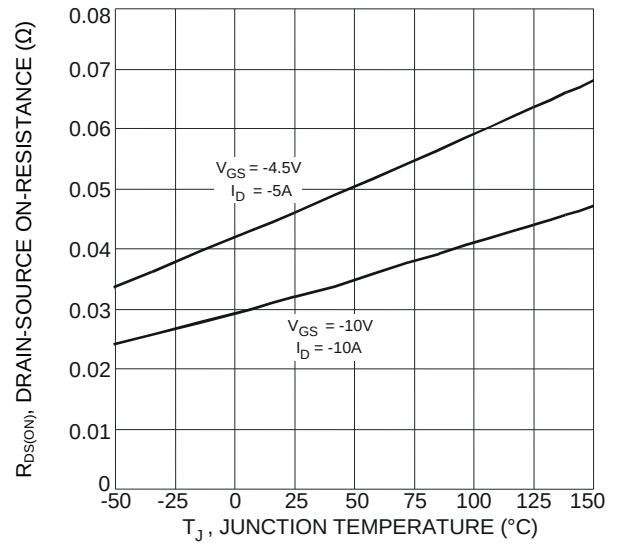


Fig. 17 On-Resistance Variation with Temperature

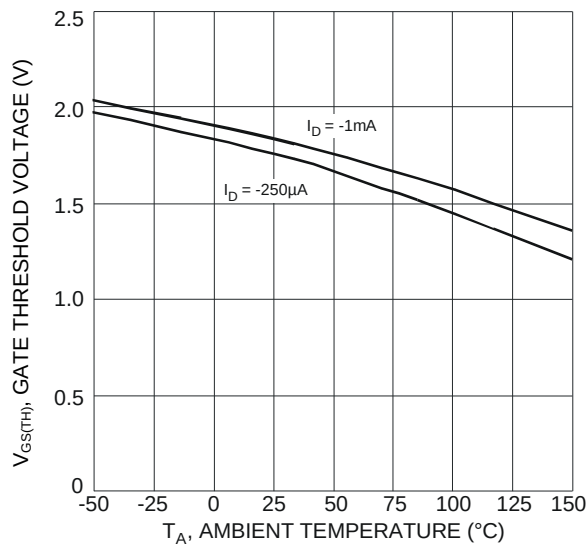


Fig. 18 Gate Threshold Variation vs. Ambient Temperature

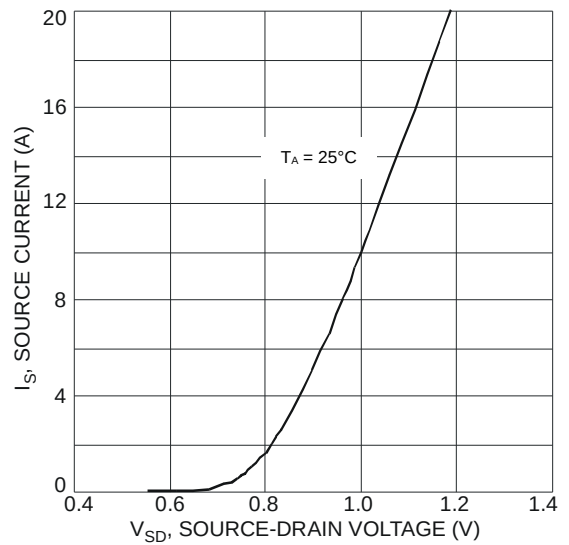
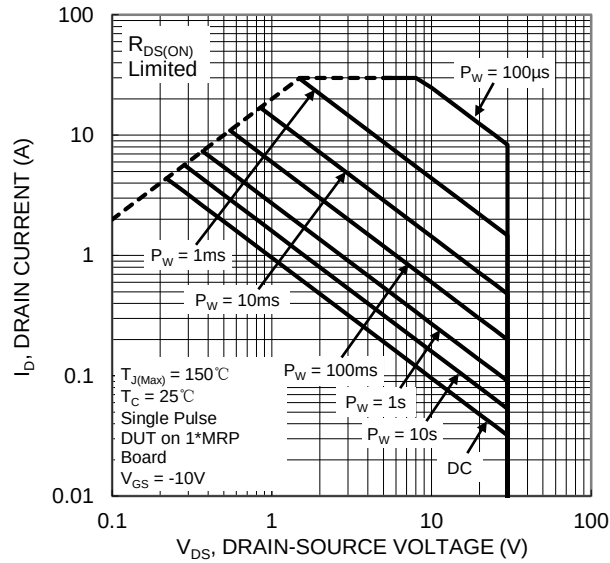
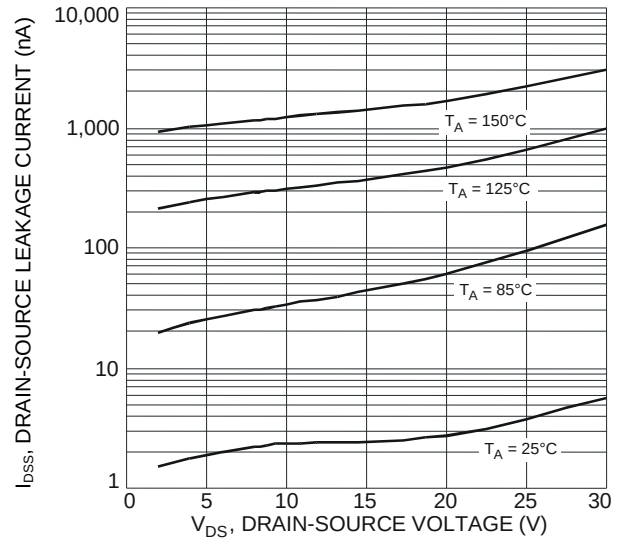
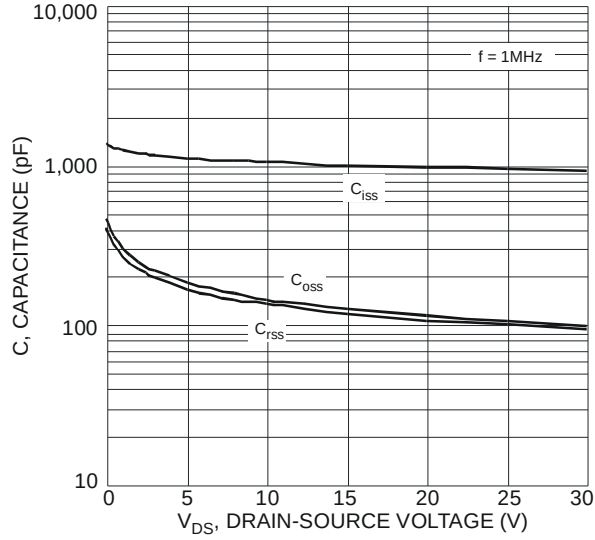


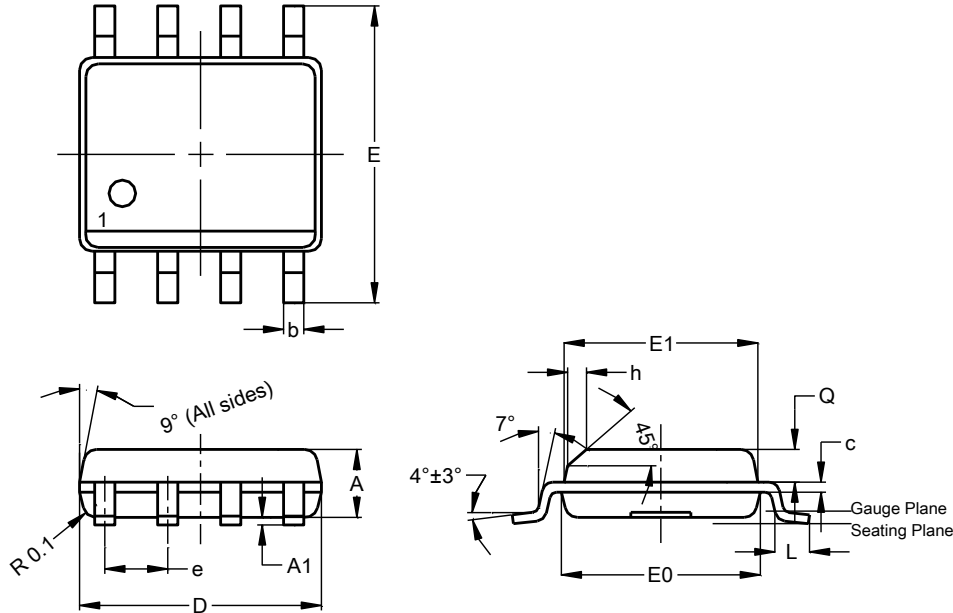
Fig. 19 Diode Forward Voltage vs. Current



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

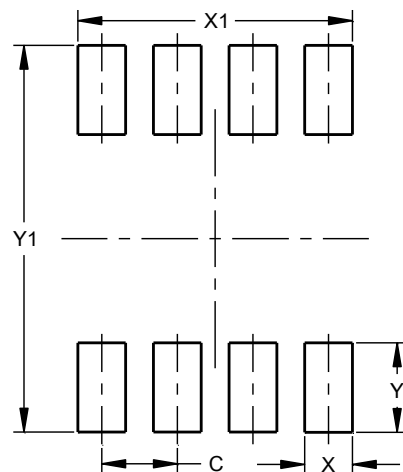


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	--	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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